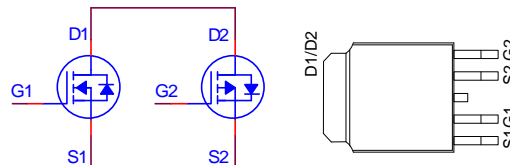


PRODUCT SUMMARY

	$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
N-Channel	30	20m Ω	25A
P-Channel	-30	36m Ω	-19A



G : GATE
D : DRAIN
S : SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	N-Channel	P-Channel	UNITS
Drain-Source Voltage		V _{DS}	30	-30	V
Gate-Source Voltage		V _{GS}	±20	±20	V
Continuous Drain Current	T _C = 25 °C	I _D	25	-19	A
	T _C = 70 °C		20	-15	
	T _A = 25 °C		9	-7	
	T _A = 70 °C		7	-5.7	
Pulsed Drain Current ²		I _{DM}	65	-45	
Avalanche Current		I _{AS}	19	-18	
Avalanche Energy	L = 0.1mH	E _{AS}	18	17	mJ
Power Dissipation	T _C = 25 °C	P _D	21		W
	T _C = 70 °C		13		
	T _A = 25 °C		3		
	T _A = 70 °C		2		
Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150		°C
Lead Temperature (¹ / ₁₆ " from case for 10 sec.)		T _L	275		

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		6	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		42	$^\circ\text{C} / \text{W}$

¹ Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	N-Ch	30		V
		$V_{GS} = 0V, I_D = -250\mu A$	P-Ch	-30		

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	N-Ch	1	1.7	2.5	
		$V_{DS} = V_{GS}, I_D = -250\mu A$	P-Ch	-1	-1.6	-2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	N-Ch			± 100	nA
		$V_{DS} = 0V, V_{GS} = \pm 20V$	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$	N-Ch			1	μA
		$V_{DS} = -24V, V_{GS} = 0V$	P-Ch			-1	
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 55^\circ C$	N-Ch			10	
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 55^\circ C$	P-Ch			-10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	N-Ch	65			A
		$V_{DS} = -5V, V_{GS} = -10V$	P-Ch	-45			
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 6A$	N-Ch		26	31	m Ω
		$V_{GS} = -4.5V, I_D = -5A$	P-Ch		58	61	
		$V_{GS} = 10V, I_D = 7A$	N-Ch		17	20	
		$V_{GS} = -10V, I_D = -6A$	P-Ch		35	36	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 10V, I_D = 7A$	N-Ch		29		S
		$V_{DS} = -10V, I_D = -6A$	P-Ch		15		

DYNAMIC							
Input Capacitance	C_{iss}	N-Channel	N-Ch		480		
			P-Ch		691		
Output Capacitance	C_{oss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$ P-Channel	N-Ch		162		pF
			P-Ch		167		
Reverse Transfer Capacitance	C_{rss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$	N-Ch		100		
			P-Ch		117		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$	N-Ch		2		Ω
			P-Ch		6.27		
Total Gate Charge ²	Q_g	N-Channel $V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$ $I_D = 6A$	N-Ch		9.8		nC
Gate-Source Charge ²	Q_{gs}		P-Ch		12.8		
Gate-Drain Charge ²	Q_{gd}	P-Channel $V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = -10V,$ $I_D = -5A$	N-Ch		2.1		
			P-Ch		2.9		
			N-Ch		1.8		
			P-Ch		2.1		

Turn-On Delay Time ²	$t_{d(on)}$	N-Channel	N-Ch		15		
		$V_{DS} = 20V$	P-Ch		15		
Rise Time ²	t_r	$I_D \cong 1A, V_{GS} = 10V, R_{GEN} = 6\Omega$	N-Ch		26		
			P-Ch		12		
Turn-Off Delay Time ²	$t_{d(off)}$	P-Channel	N-Ch		14		nS
		$V_{DS} = -20V, R_L = 1\Omega$	P-Ch		11		
Fall Time ²	t_f	$I_D \cong -1A, V_{GS} = -10V, R_{GEN} = 6\Omega$	N-Ch		21		
			P-Ch		25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25^\circ C$)							
Continuous Current	I_S		N-Ch			9	
			P-Ch			-7	A
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$	N-Ch			1	V
		$I_F = I_S, V_{GS} = 0V$	P-Ch			-1	

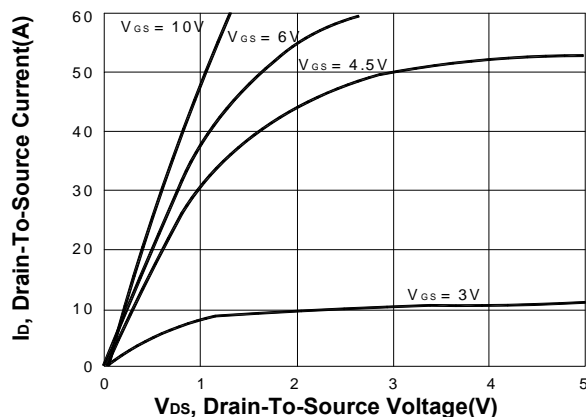
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

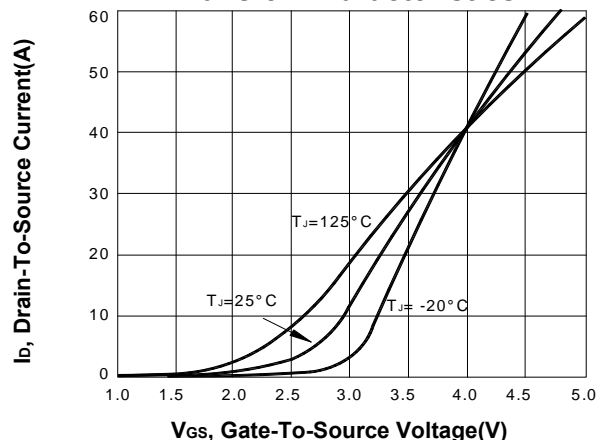
REMARK: THE PRODUCT MARKED WITH "P2003ND5G", DATE CODE or LOT #

**TYPICAL PERFORMANCE CHARACTERISTICS
N-CHANNEL**

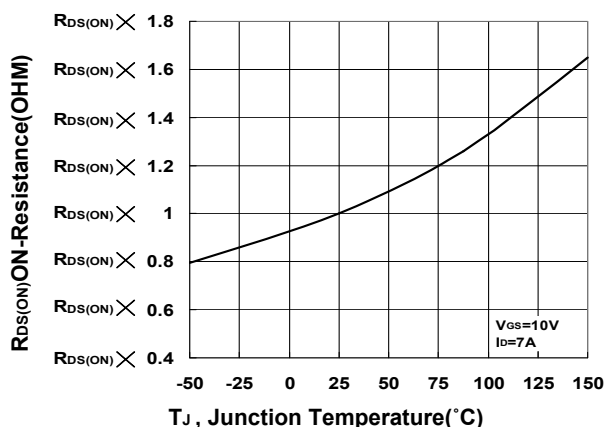
Output Characteristics



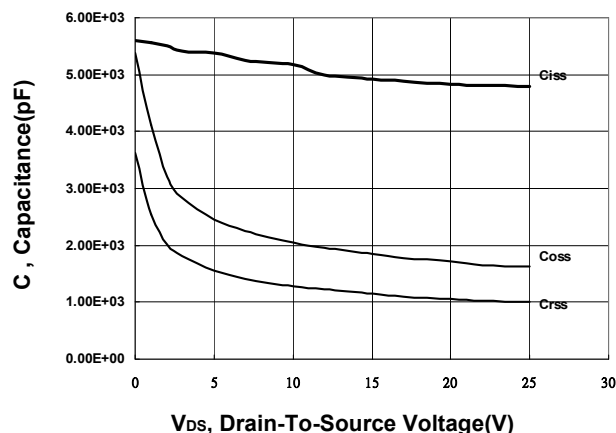
Transfer Characteristics



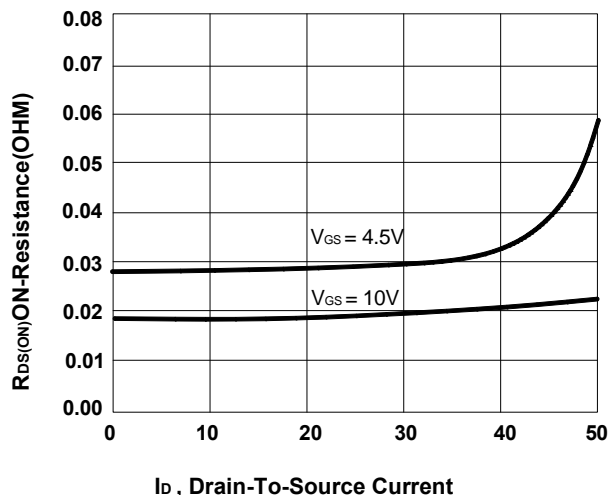
On-Resistance VS Temperature



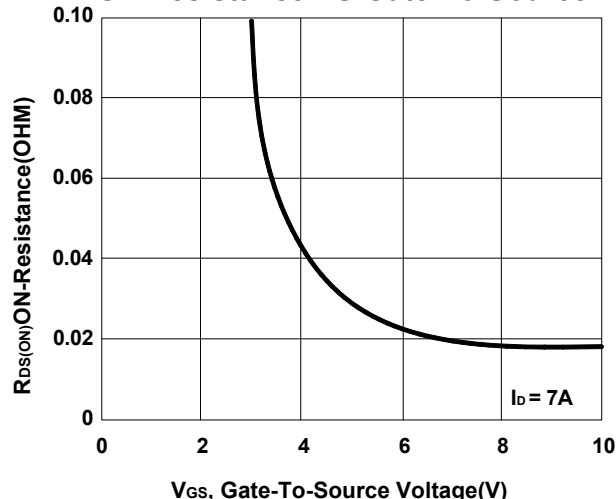
Capacitance Characteristic



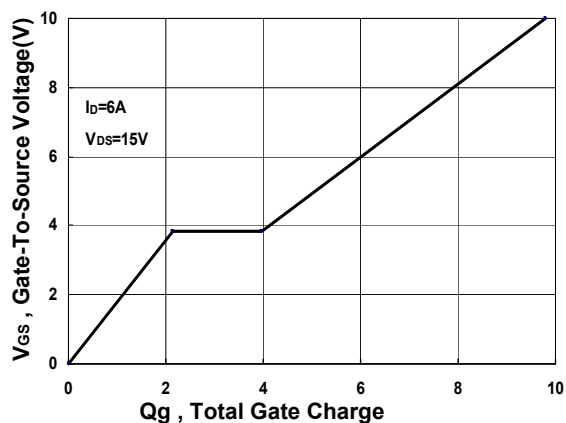
On-Resistance VS Drain Current



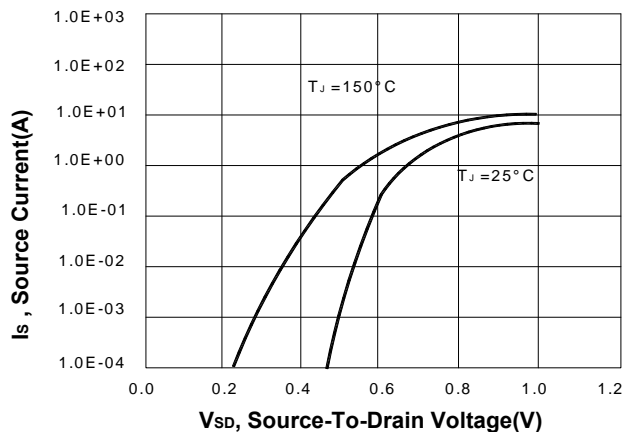
On-Resistance VS Gate-To-Source



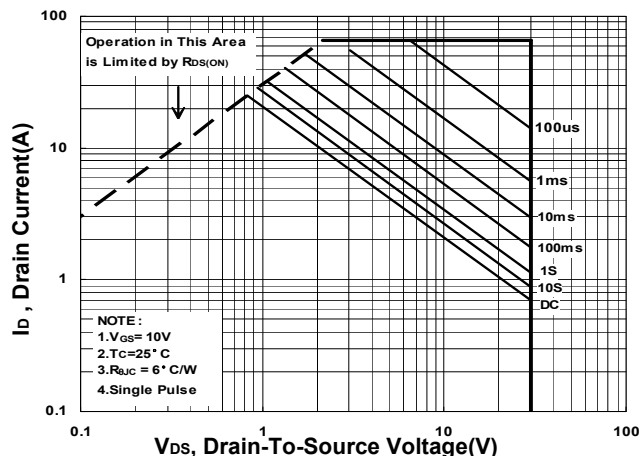
Gate charge Characteristics



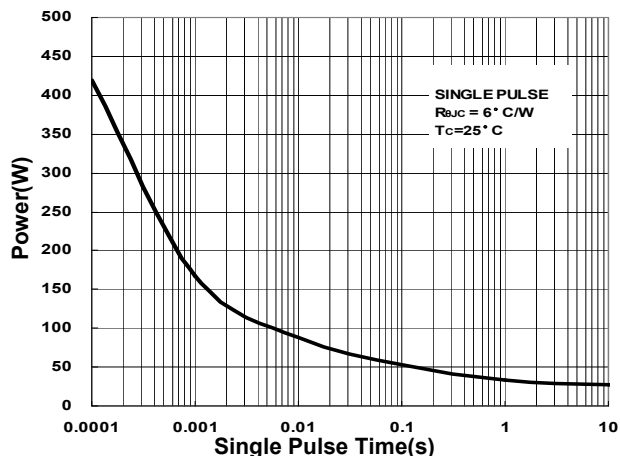
Source-Drain Diode Forward Voltage



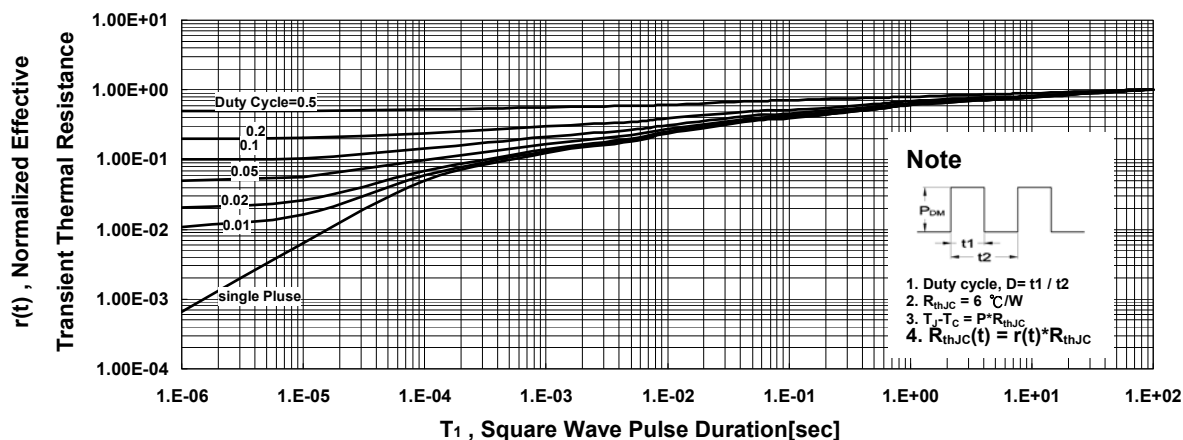
Safe Operating Area



Single Pulse Maximum Power Dissipation

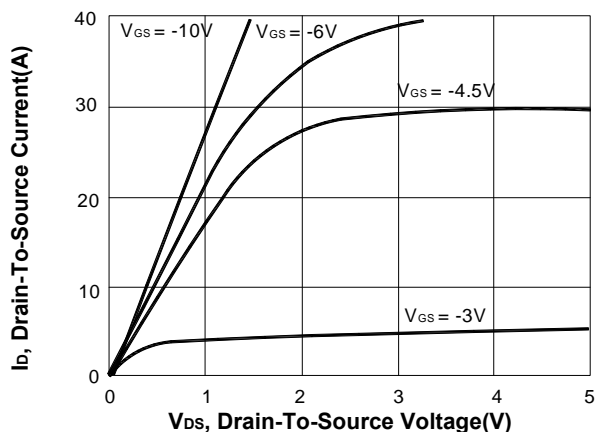


Transient Thermal Response Curve

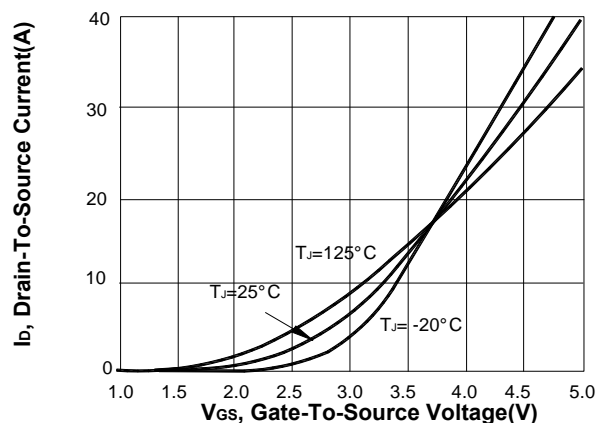


P-CHANNEL

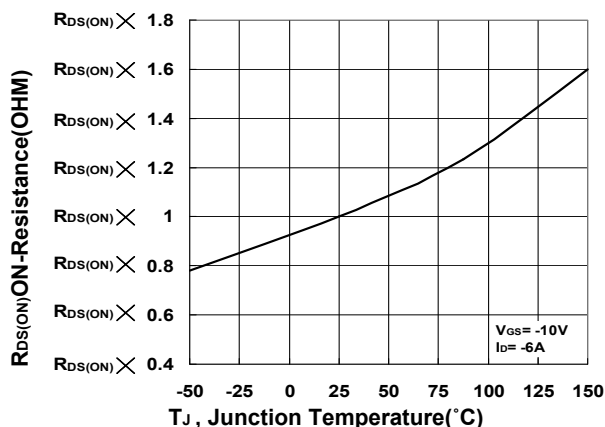
Output Characteristics



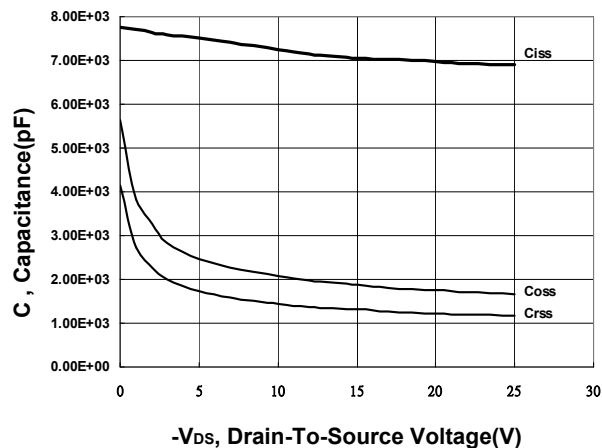
Transfer Characteristics



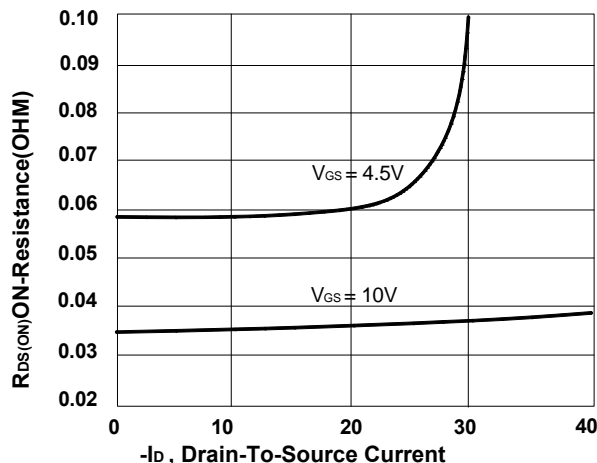
On-Resistance VS Drain-Current



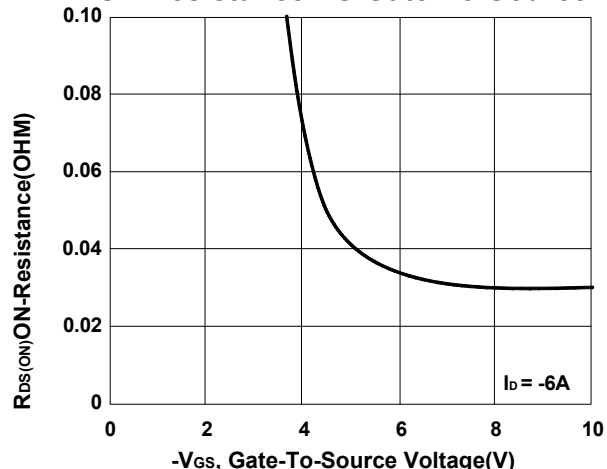
Capacitance Characteristic



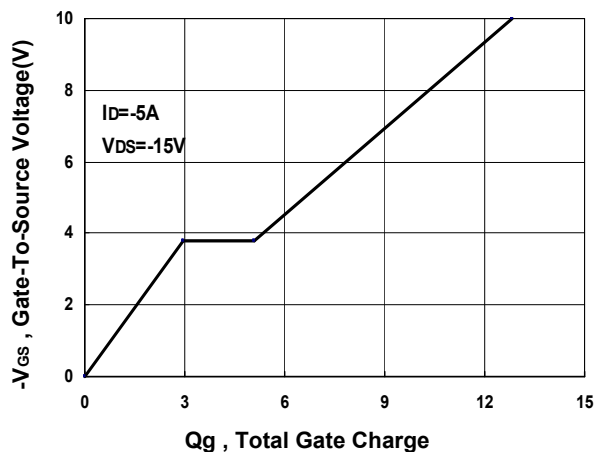
On-Resistance VS Drain Current



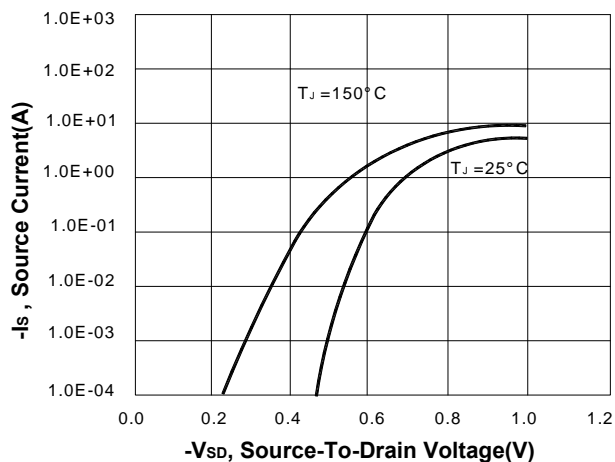
On-Resistance VS Gate-To-Source



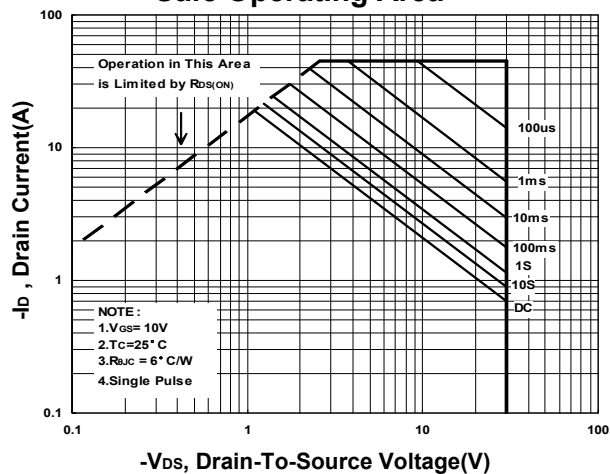
Gate charge Characteristics



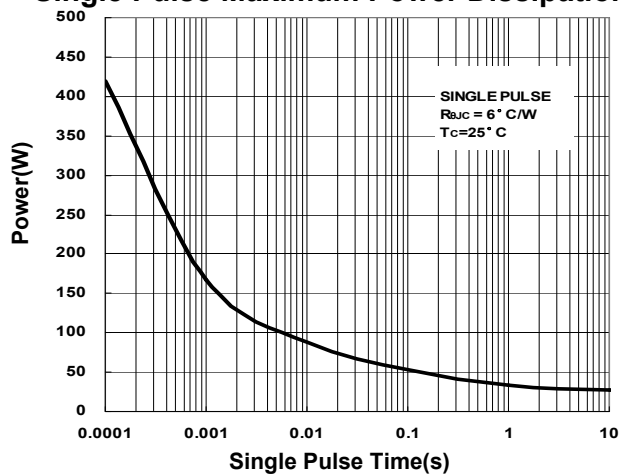
Source-Drain Diode Forward Voltage



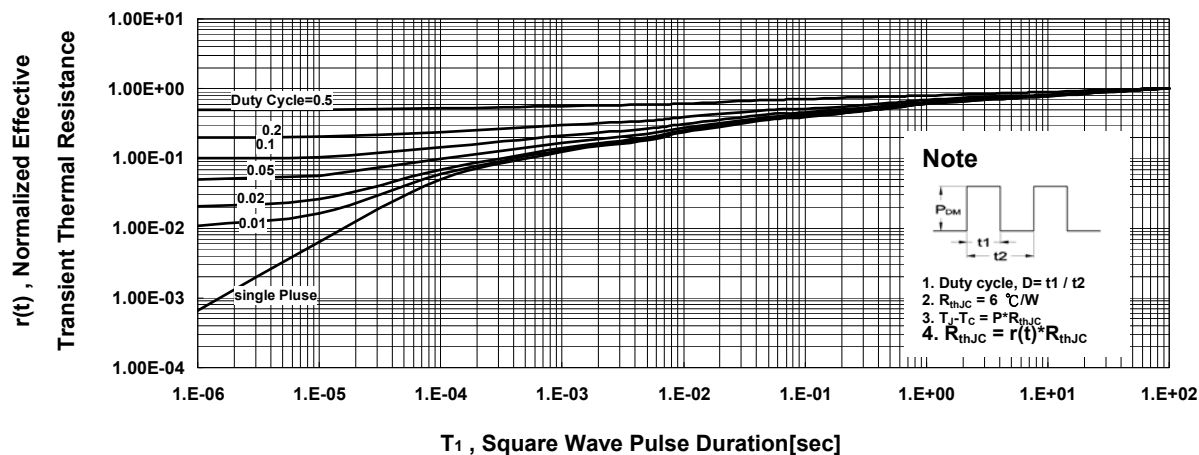
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



TO-252-4 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.0	9.5	10.4	H	0.9	1.5	1.7
B	2.1	2.3	2.5	I	6.3	6.5	6.8
C	0.4	0.5	0.6	J	4.8	5.0	5.5
D	0.95	1.2	1.3	K	1.0	1.3	1.6
E	0.4	0.5	0.6	L	0.3	0.5	0.7
F	0.0		0.3	M	1.1	1.3	1.5
G	5.3	5.5	6.2	N			

